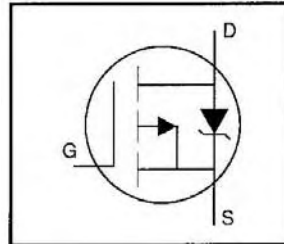


IRFR9220PbF IRFU9220PbF

- Dynamic dv/dt Rating
- Repetitive Avalanche Rated
- Surface Mount (IRFR9220)
- Straight Lead (IRFU9220)
- Available in Tape & Reel
- P-Channel
- Fast Switching
- Lead-Free



$$V_{DSS} = -200V$$

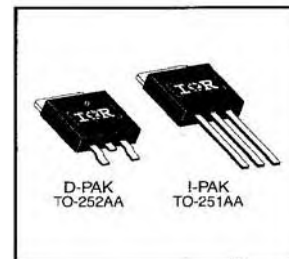
$$R_{DS(on)} = 1.5\Omega$$

$$I_D = -3.6A$$

Description

The HEXFET technology is the key to International Rectifier's advanced line of power MOSFET transistors. The efficient geometry and unique processing of the HEXFET design achieve very low on-state resistance combined with high transconductance and extreme device ruggedness.

The D-Pak is designed for surface mounting using vapor phase, infrared, or wave soldering techniques. The straight lead version (IRFU series) is for through-hole mounting applications. Power dissipation levels up to 1.5 watts are possible in typical surface mount applications.



Absolute Maximum Ratings

	Parameter	Max.	Units
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ -10 V$	-3.6	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ -10 V$	-2.3	
I_{DM}	Pulsed Drain Current ①	-14	
$P_D @ T_C = 25^\circ C$	Power Dissipation	42	W
$P_D @ T_A = 25^\circ C$	Power Dissipation (PCB Mount)**	2.5	
	Linear Derating Factor	0.33	W/°C
	Linear Derating Factor (PCB Mount)**	0.020	
V_{GS}	Gate-to-Source Voltage	± 20	V
E_{AS}	Single Pulse Avalanche Energy ②	310	mJ
I_{AR}	Avalanche Current ①	-3.6	A
E_{AR}	Repetitive Avalanche Energy ①	4.2	mJ
dv/dt	Peak Diode Recovery dv/dt ③	-5.0	V/ns
T_J, T_{STG}	Junction and Storage Temperature Range	-55 to +150	°C
	Soldering Temperature, for 10 seconds	260 (1.6mm from case)	

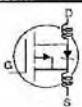
Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	—	3.0	°C/W
$R_{\theta JA}$	Junction-to-Ambient (PCB mount)**	—	—	50	
$R_{\theta JA}$	Junction-to-Ambient	—	—	110	

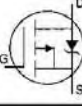
** When mounted on 1" square PCB (FR-4 or G-10 Material).

For recommended footprint and soldering techniques refer to application note #AN-994.

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Test Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	-200	—	—	V	$V_{GS}=0V$, $I_D=-250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	-0.22	—	V/ $^\circ\text{C}$	Reference to 25°C , $I_D=-1mA$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	1.5	Ω	$V_{GS}=-10V$, $I_D=-2.2A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	-2.0	—	-4.0	V	$V_{DS}=V_{GS}$, $I_D=-250\mu A$
g_{fs}	Forward Transconductance	1.1	—	—	S	$V_{DS}=-50V$, $I_D=-2.2A$ ④
I_{DSS}	Drain-to-Source Leakage Current	—	—	-100	μA	$V_{DS}=-200V$, $V_{GS}=0V$
		—	—	-500		$V_{DS}=-160V$, $V_{GS}=0V$, $T_J=125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	-100	nA	$V_{GS}=-20V$
	Gate-to-Source Reverse Leakage	—	—	100		$V_{GS}=20V$
Q_g	Total Gate Charge	—	—	20	nC	$I_D=-3.9A$
Q_{gs}	Gate-to-Source Charge	—	—	3.3		$V_{DS}=-160V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	—	11		$V_{GS}=-10V$ See Fig. 6 and 13 ④
$t_{d(on)}$	Turn-On Delay Time	—	8.8	—	ns	$V_{DD}=-100V$
t_r	Rise Time	—	27	—		$I_D=-3.9A$
$t_{d(off)}$	Turn-Off Delay Time	—	7.3	—		$R_G=18\Omega$
t_f	Fall Time	—	19	—		$R_D=24\Omega$ See Figure 10 ④
L_D	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6 mm (0.25in.) from package and center of die contact 
L_S	Internal Source Inductance	—	7.5	—		
C_{iss}	Input Capacitance	—	340	—	pF	$V_{GS}=0V$
C_{oss}	Output Capacitance	—	110	—		$V_{DS}=-25V$
C_{rss}	Reverse Transfer Capacitance	—	33	—		$f=1.0MHz$ See Figure 5

Source-Drain Ratings and Characteristics

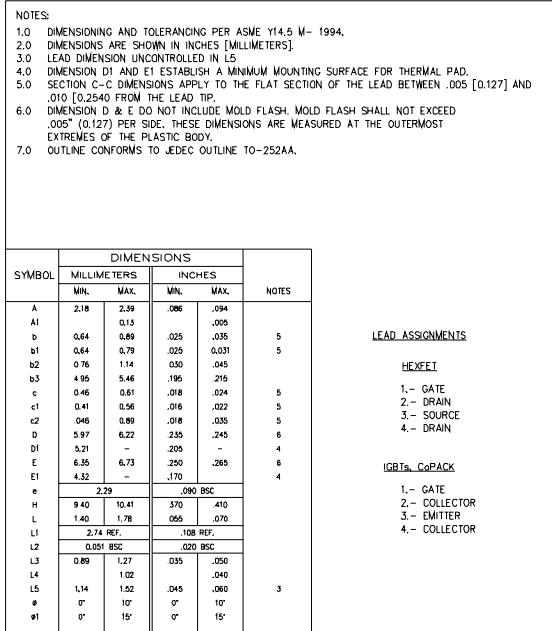
	Parameter	Min.	Typ.	Max.	Units	Test Conditions
I_S	Continuous Source Current (Body Diode)	—	—	-3.6	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	-14		
V_{SD}	Diode Forward Voltage	—	—	-6.3	V	$T_J=25^\circ\text{C}$, $I_S=-3.6A$, $V_{GS}=0V$ ②
t_{rr}	Reverse Recovery Time	—	150	300	ns	$T_J=25^\circ\text{C}$, $I_F=-3.9A$
Q_{rr}	Reverse Recovery Charge	—	0.97	2.0	μC	$di/dt=100A/\mu s$ ④
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L_S+L_D)				

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature (See Figure 11)
- ② $V_{DD}=-50V$, starting $T_J=25^\circ\text{C}$, $L=35mH$, $R_G=25\Omega$, $I_{AS}=-3.6A$ (See Figure 12)
- ③ $I_{SD}\leq 3.9A$, $di/dt\leq 95A/\mu s$, $V_{DD}\leq V_{(BR)DSS}$, $T_J\leq 150^\circ\text{C}$
- ④ Pulse width $\leq 300\mu s$; duty cycle $\leq 2\%$.

International
IOR Rectifier

Dimensions are shown in millimeters (inches)



EXAMPLE: THIS IS AN IRFR120
WITH ASSEMBLY
LOT CODE 1234
ASSEMBLED ON WW 16, 1999
IN THE ASSEMBLY LINE "A"

Diagram illustrating the marking on the IRFU120 diode package:

- INTERNATIONAL RECTIFIER LOGO
- PART NUMBER: IRFU120
- DATE CODE: 12 34
- YEAR 9 = 1999
- WEEK 16
- LINE A
- ASSEMBLY LOT CODE

INTERNATIONAL RECTIFIER LOGO

PART NUMBER

DATE CODE

P = DESIGNATES LEAD-FREE PRODUCT (OPTIONAL)

YEAR 9 = 1999

WEEK 16

A = ASSEMBLY SITE CODE

IRF120

P916A

12 34

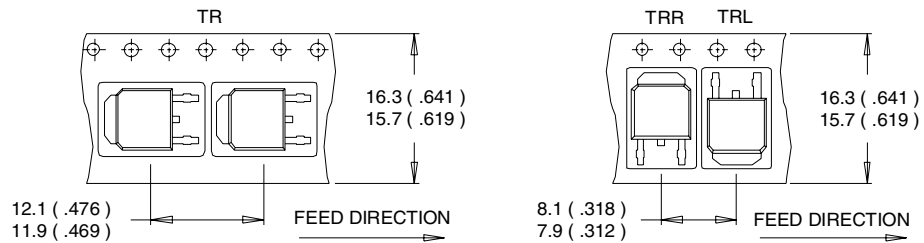
ASSEMBLY LOT CODE

IRFR/U9220PbF

International
IR Rectifier

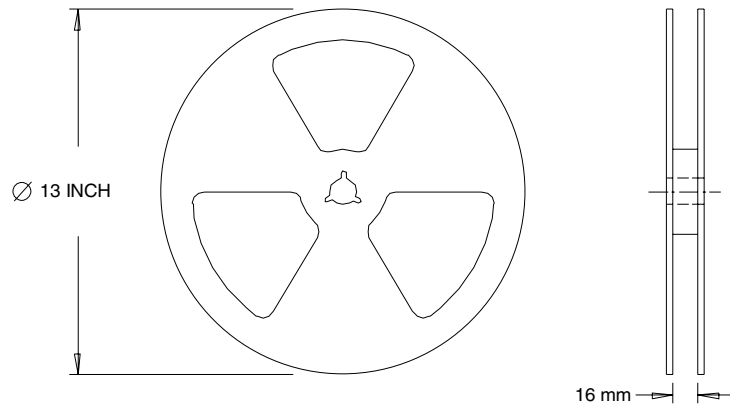
D-Pak (TO-252AA) Tape & Reel Information

Dimensions are shown in millimeters (inches)



NOTES :

1. CONTROLLING DIMENSION : MILLIMETER.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



NOTES :

1. OUTLINE CONFORMS TO EIA-481.

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